

SANYO Semiconductors DATA SHEET

N-Channel Silicon MOSFET

CPH6612— General-Purpose Switching Device Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- 1.8V drive.
- · Composite type with 2 MOSFETs contained in a single package, facilitating high-density mounting.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		20	V
Gate-to-Source Voltage	VGSS		±12	V
Drain Current (DC)	ID		2	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	8	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)1unit	0.8	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0			1	μΑ
Gate-to-Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0			±10	μΑ
Cutoff Voltage	VGS(off)	VDS=10V, ID=1mA	0.4		1.3	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =1A	1.4	2.4		S
Static Drain-to-Source On-State Resistance	R _{DS} (on)1	I _D =1A, V _{GS} =4V		125	165	mΩ
	RDS(on)2	ID=0.5A, VGS=2.5V		165	235	mΩ
	R _{DS} (on)3	I _D =0.1A, V _G S=1.8V		230	350	mΩ
Input Capacitance	Ciss	VDS=10V, f=1MHz		120		pF
Output Capacitance	Coss	VDS=10V, f=1MHz		31		pF
Reverse Transfer Capacitance	Crss	V _{DS} =10V, f=1MHz		25		pF

Marking: FY Continued on next page.

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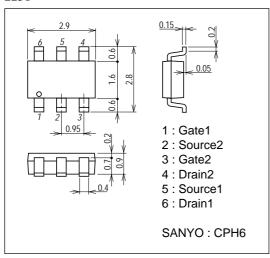
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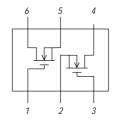
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Turn-ON Delay Time	t _d (on)	See specified Test Circuit		9		ns
Rise Time	t _r	See specified Test Circuit		29		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		18		ns
Fall Time	tf	See specified Test Circuit		22		ns
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =4V, I _D =2A		2.3		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =4V, I _D =2A		0.5		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =4V, I _D =2A		0.75		nC
Diode Forward Voltage	V _{SD}	I _S =2A, V _{GS} =0		0.94	1.2	V

Package Dimensions

unit : mm 2238



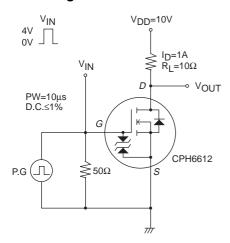
Electrical Connection

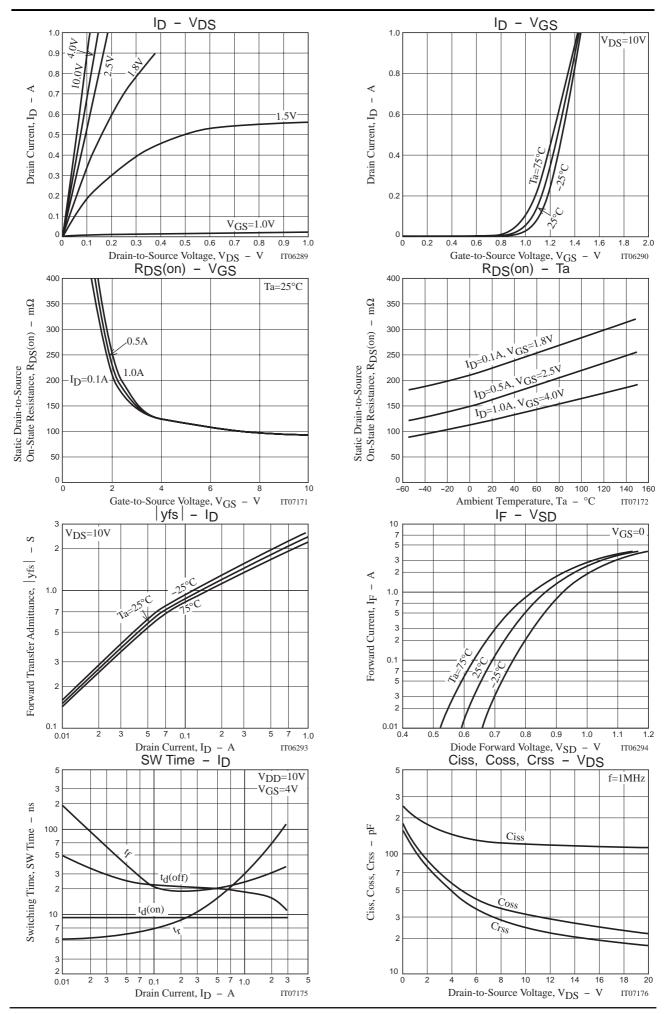


1 : Gate1 2 : Source2 3 : Gate2 4 : Drain2 5 : Source1 6 : Drain1

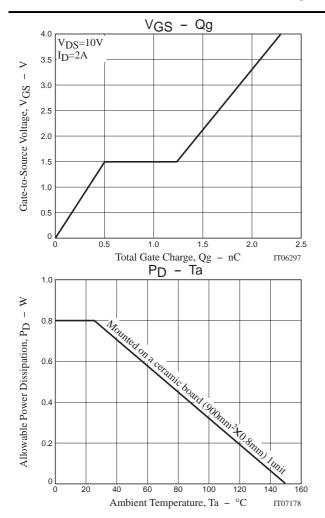
Top view

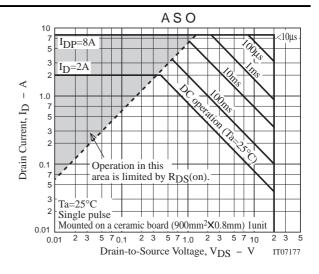
Switching Time Test Circuit





CPH6612





Note on usage: Since the CPH6612 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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